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Quantum plasmons with optical-range frequencies in doped few-layer graphene

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Abstract

Although plasmon modes exist in doped graphene, the limited range of doping achieved by gating restricts the plasmon frequencies to a range that does not include visible and infrared. Here we show, through the use of first-principles calculations, that the high levels of doping achieved by lithium intercalation in bilayer and trilayer graphene shift the plasmon frequencies into the visible range. To obtain physically meaningful results, we introduce a correction of the effect of plasmon interaction across the vacuum separating periodic images of the doped graphene layers, consisting of transparent boundary conditions in the direction perpendicular to the layers; this represents a significant improvement over the Exact Coulomb cutoff technique employed in earlier works. The resulting plasmon modes are due to local field effects and the non-local response of the material to external electromagnetic fields, requiring a fully quantum mechanical treatment. We describe the features of these quantum plasmons, including the dispersion relation, losses and field localization. Our findings point to a strategy for fine-tuning the plasmon frequencies in graphene and other two dimensional materials.

11 Collective excitations of electrons in metals, generically referred to as plasmons, have
12 been attracting new attention recently in the realm of nanoparticles and low-dimensional
13 materials. In these systems, new plasmonic phenomena continue to be discovered, be-
14 yond what was observed in conventional crystalline solids. These phenomena include
15 quantum interference of plasmons, observation of quantum coupling of plasmons to sin-
16 gle particle excitations, and quantum confinement of plasmons in nm-scale particles and
17 materials. These phenomena, intriguing in their own right, are also important for mul-
18 tifaceted applications. Plasmonic nanostructures are finding applications in integrated
19 nanophotonics¹, biosensing²⁻⁴, photovoltaic devices⁵⁻⁷, single photon transistors⁸, single
20 molecule spectroscopy⁹ and metamaterials^{10,11}. The current interest in quantum nanopho-
21 tonics and plasmonics is in part driven by new materials, particularly low dimensional solids,
22 that access new ranges of frequency and transmission speeds. The reduced dimensionality
23 of plasmons in two-dimensional (2D) materials provides ultra-subwavelength confinement
24 with phase velocities several orders of magnitude lower than the speed of light¹². In the
25 present work we show that by properly controlling the density of metallic electrons in few-
26 layer graphene, the prototypical 2D metal, the plasmon frequency can be pushed into the
27 visible to near-infrared range, a feature highly desirable for optoelectronic applications and
28 heretofore unattainable.

29 Graphene is quite special for 2D plasmonics¹³, exhibiting intriguing properties such as ex-
30 tremely high electrical mobility¹⁴ and easily tunable electron and hole doping concentrations
31 (n_e, n_h), through gating^{14,15}. The plasmon frequencies in graphene are controlled through
32 doping¹³, where typical doping concentration values achieved by gating are $\approx 10^{11} \text{ cm}^{-2}$, and
33 the heaviest doping reached¹⁶ is $n_h > 10^{13} \text{ cm}^{-2}$. Plasmons in gate-doped graphene typically
34 emerge in the infrared to THz ranges, and seldom in the mid- or near-infrared range^{4,16,17}.
35 So far, reaching the visible range for 2D plasmons in graphene, a crucial requirement for
36 optoelectronic applications, has remained elusive. Searching for materials beyond graphene
37 to achieve plasmons with optical frequencies is a possible route. For example, one possibil-
38 ity is the family of 2D materials referred to as transition metal dichalcogenides (TMDCs),
39 but plasmons in these materials are predicted to appear at THz frequencies^{18,19}. Another
40 possible solution, the plasmon mode on Be(0001)¹³ observed in the visible range²⁰, cannot
41 be interpreted as a true 2D plasmon, since it has finite penetration depth into the under-
42 lying bulk material. A recent report by Huang *et al.*²¹ predicts that triangular polymorph

43 of 2D boron sheet exhibits visible frequency plasmons. But free-standing triangular 2D
44 boron is dynamically unstable²² and its experimental synthesis quite difficult, which makes
45 it challenging for device applications.

46 We propose here an alternative approach for breaking the impasse, by doping few-layer
47 graphene structures to levels beyond what is achievable through gating. Though there have
48 been previous reports of optical-frequency plasmons in graphene monolayers with adsorbed
49 Li atoms (LiC_2)²³, this configuration is energetically unstable as we have established in
50 previous work²⁴, and therefore unlikely to form experimentally; encapsulating the Li atoms
51 between graphene layers, as in the structures proposed and studied here, is required to stabi-
52 lize the doped system. Experiments have proved the feasibility of inserting metal atoms like
53 lithium (Li) between layers of 2D materials^{25,26} resulting in heavy doping. Inspired by this,
54 we use a theoretical approach based on first-principles electronic structure calculations to
55 explore the possibility of observing quantum plasmons in the visible range for Li-intercalated
56 two- and three-layer graphene. The origin of 2D plasmons is related to the local field effects
57 and the non-local response of the material to external fields²⁷. Hence, the study of these
58 waves demands a fully quantum mechanical description of the material properties which
59 compels us to call them as ‘quantum’ 2D plasmons. We effectively capture the quantum
60 nature of these plasmons through our accurate, high-fidelity first-principles calculations, dis-
61 tinguished by: (i) our methodology which correctly confines plasmons in two dimensions,
62 and (ii) a realistic estimate of carrier lifetime, a crucial factor that determines plasmon
63 losses. Our results show that quantum plasmons in few-layer graphene are indeed feasible.
64 This opens new pathways for fine-tuning a wide range of plasmon frequencies, including the
65 visible range, in 2D structures, by controlling the concentration and type of intercalants.

66 Our first-principles calculations are based on density functional theory (DFT) as imple-
67 mented in the GPAW package^{28,29}. The interaction between ionic cores and valence electrons
68 is described by the projector augmented wave method^{30,31}. A vacuum of 25 Å is included
69 to minimize the interaction between periodic images along the direction perpendicular to
70 the plane of the sheets (z direction). The Kohn-Sham wavefunctions are represented using
71 a plane wave basis with energy cutoff of 340 eV, and the exchange correlation energy of
72 electrons is described using Local Density Approximated (LDA) functional. For the linear
73 response calculations, used to estimate the dielectric functions³², we sample the Brillouin
74 zone with a $256 \times 256 \times 1$ grid of k -points to include an accurate description of intraband

75 transitions. For the dielectric response calculations we use a plane wave energy cutoff of 30
 76 eV. All the other parameters were converged to within 0.05 eV of the plasmon energies, us-
 77 ing the methodology developed by Andersen *et al.*^{18,33} for calculating the quantum plasmon
 78 modes.

79 The potential $\phi(\mathbf{r}, \omega)$ and charge density $\rho(\mathbf{r}, \omega)$ of the quantum plasmon modes, are
 80 obtained as left and right eigenfunctions (which satisfy the Poisson equation) of the dielectric
 81 operator $\hat{\epsilon}(\omega)$, diagonalized in the plane wave basis:

$$\hat{\epsilon}(\omega)\phi_n(\omega) = [\hat{1} - \hat{v} \hat{\chi}^0(\omega)]\phi_n(\omega) = \lambda_n(\omega)\phi_n(\omega), \quad (1)$$

82 where ω and \mathbf{r} denote the frequency and in-plane spatial vector, respectively. Here, $\hat{\epsilon}(\omega)$
 83 expressed in terms of the noninteracting linear response operator $\hat{\chi}^0(\omega)$ and the Coulomb
 84 interaction operator $\hat{v} = 1/|\mathbf{r} - \mathbf{r}'|$. The condition for observing a plasmon at frequency ω_p
 85 is $\text{Re}[\lambda_n(\omega)] = 0$ or equivalently a peak in the loss function, $-\text{Im}[\lambda_n(\omega)]/|\lambda_n(\omega)|^2$.

86 A key ingredient in obtaining the plasmon dispersion relations and losses is the carrier
 87 lifetime, τ . To obtain reliable values of τ , we used DFT results for the energies and matrix
 88 elements of both electrons and phonons (see Supplemental Material³⁴ and³⁵). This takes
 89 into account the detailed electronic structure effects such as response of electrons far from
 90 the Dirac point, as well as scattering against both acoustic and optical phonons including
 91 Umklapp and inter-valley processes³⁵⁻³⁸. Doping, that is, change in position of the Fermi
 92 level (E_F), changes the value of τ , and hence calculations were carried out for several different
 93 values of E_F ranging from the neutral (undoped) value to 1.5 eV above it (see Supplemental
 94 Material³⁴ for details of formulation and³⁵ for values of τ). Interestingly, our results show
 95 that the extremely large $\tau \approx 1$ ps for free standing undoped graphene drops to ≈ 29 fs in
 96 doped graphene. For simplicity and computational efficiency, we use a doped monolayer
 97 graphene to obtain the values of τ for positions of E_F that correspond to those of the Li-
 98 doped bilayer and trilayer graphene; this is a reasonable approximation, because, at high
 99 doping concentrations, we expect that the effects of interlayer electron-phonon and electron-
 100 electron coupling on τ in intercalated graphene will be rather small compared to the effects
 101 of changing the position of E_F , which is properly taken into account by the procedure
 102 described.

103 The standard approach for eliminating spurious effects due to finite size of vacuum³⁹ is
 104 inadequate for plasmons with small in-plane wavenumbers (\mathbf{q}), and increasing the size of the

105 vacuum region until these effects become negligibly small requires very expensive calcula-
 106 tions. A significant methodological contribution of the present work is the formulation and
 107 implementation of transparent boundary conditions which overcome the drawbacks of the
 108 Coulomb cutoff method and offer a more accurate description of the quantum plasmon fields.
 109 Let z_-, z_+ be the bounds of the super-cell (simulation box) along the z direction (vacuum
 110 region) with (x, y) plane being periodic. We apply a one-dimensional Fourier transform
 111 in the z direction to obtain a real space representation in this coordinate. The response
 112 operator under random phase approximation (RPA) then has the form:

$$\hat{\chi}^0 \phi(z, \mathbf{G}_{xy}, \mathbf{q}, \omega) = \int_{z_-}^{z_+} \sum_{\mathbf{G}'_{xy}} \chi_{\mathbf{G}_{xy}, \mathbf{G}'_{xy}}^0(z, z', \mathbf{q}, \omega) \phi(z', \mathbf{G}'_{xy}, \mathbf{q}, \omega) dz', \quad (2)$$

113 where $\mathbf{G}_{xy}, \mathbf{G}'_{xy}$ are vectors of the in-plane reciprocal lattice For values of z, z' inside the
 114 super-cell, $z_- < z, z' < z_+$, the kernel $\chi_{\mathbf{G}_{xy}, \mathbf{G}'_{xy}}^0(z, z')$ is deduced from $\chi_{\mathbf{G}, \mathbf{G}'}^0$ by Fourier
 115 transform. The kernel is extended with zero values for z or z' that lie in the vacuum region
 116 outside this cell. We observe that Eq. (1) can be reformulated as the generalized eigenvalue
 117 problem³⁴:

$$\hat{\chi}^0 \phi_n(z, \mathbf{G}_{xy}, \mathbf{q}, \omega) = \frac{1 - \lambda_n}{4\pi} \left(|\mathbf{q} + \mathbf{G}_{xy}|^2 - \frac{\partial^2}{\partial z^2} \right) \phi_n(z, \mathbf{G}_{xy}, \mathbf{q}, \omega), \quad (3)$$

with additional constraint that $|\phi_n| \rightarrow 0$ as $z \rightarrow \pm\infty$ so the problem is well-posed. The
 left-hand side vanishes in the vacuum region and Eq. (3) reduces to the one-dimensional
 Poisson equation. For any nonzero value of $|\mathbf{q} + \mathbf{G}_{xy}|$, we thus obtain an explicit solution

$$\phi_n(z, \mathbf{G}_{xy}, \mathbf{q}, \omega) = \phi_n(z_{\pm}, \mathbf{G}_{xy}, \mathbf{q}, \omega) e^{-|\mathbf{q} + \mathbf{G}_{xy}| |z_{\pm} - z|},$$

118 for $z \leq z_-$ and $z \geq z_+$. The continuity of ϕ_n and its first derivative with respect to z leads
 119 to the transparent boundary conditions at $z = z_{\pm}$:

$$\frac{\partial \phi_n}{\partial z}(\mathbf{q}, \mathbf{G}_{xy}, z_{\pm}, \omega) = \mp |\mathbf{q} + \mathbf{G}_{xy}| \phi_n(\mathbf{q}, \mathbf{G}_{xy}, z_{\pm}, \omega), \quad (4)$$

120 which implies that the charge density and potential do not see the periodic boundary along
 121 the z direction for any value of \mathbf{q} , and hence decay to zero as $z \rightarrow \pm\infty$. **The imposition of**
 122 **additional constraints generalizes the previous approaches^{39,40}, which makes the transparent**
 123 **boundary conditions an improvement over the former techniques.** We solve numerically by
 124 finite differences the eigenvalue problem of Eq. (3) restricted to the finite band $z_- \leq z \leq z_+$,
 125 with the boundary conditions of Eq.(4) (see Supplemental Material for details³⁴).

126 We model Li intercalated graphene (G) multilayers with an in-plane $\sqrt{3} \times \sqrt{3}$ multiple of
 127 the primitive unit cell of graphene, with the G/Li/G (bilayer) and G/Li/G/Li/G (trilayer)
 128 structures. There is one Li atom per unit cell between each pair of layers (see Fig. 1)^{24,41}.
 129 For the trilayer, we consider the structure with the two Li atoms at the same hollow site
 130 but between two different pairs of graphene layers, as this is the most stable configuration⁴¹.
 131 Li intercalation makes AA stacking energetically more preferable²⁴ and hence both bilayer
 132 and trilayer structures are inversion symmetric. The separation between the layers increases
 133 by 0.14 Å and 0.11 Å relative to its value in the AA stacked graphene bilayer (3.52 Å), for
 134 the bilayer and trilayer, respectively. Due to band folding in the $\sqrt{3} \times \sqrt{3}$ unit cell, the
 135 high symmetry K point and hence the Dirac point of primitive graphene cell folds onto Γ
 136 point in the Brillouin zone (BZ) in our simulations (see Fig. 1). AA stacking preserves the
 137 sublattice symmetry of the layers and the linear dispersion of the electron bands at the Dirac
 138 point, unlike AB stacking where the bands are parabolic⁴². Intercalation also leads to charge
 139 transfer from Li to the graphene layers, and renders the system metallic (see Fig. 1) with \approx
 140 0.84e and 0.87e charge transferred from Li to bilayer and trilayer graphene (determined using
 141 Bader analysis), which corresponds to $n = 5 \times 10^{14}$ and $n = 10^{15}$, respectively. Subsequently,
 142 shifting the Fermi level from the Dirac point into the conduction band by 1.35 eV and by
 143 1.51 eV for the bilayer and trilayer, respectively, as seen in Fig. 1.

144 Since we consider metallic multilayers, more than one plasmon modes emerge^{18,33,42}. De-
 145 pending on the phase of the charge density and potential fields, we differentiate them as
 146 symmetric and antisymmetric plasmonic modes [see Fig. 2(a) and (d)]. For small \mathbf{q} , the
 147 decay length of 2D plasmons extends beyond the vacuum region giving rise to interactions
 148 with periodic images, and hence, spurious fields and pseudo charges at the vacuum edge. On
 149 the other hand, our transparent boundary conditions correct these periodic interactions and
 150 make the plasmon tails invisible to one another for the same vacuum length. The charge
 151 density with (solid lines) and without (dotted lines) transparent boundary conditions is
 152 shown in Fig. 2(a) and (d) for G/Li/G and G/Li/G/Li/G, respectively. We also note that
 153 the charge transferred from Li is equally distributed in the unoccupied π^* orbitals, which is
 154 confirmed from the charge density distribution of the plasmon modes [see in Fig. 2(a) and
 155 (d)], where the intensity of the fields is equal and reaches the maximum/minimum values
 156 away from the layers, consistent with the fact that the π^* orbitals of graphene extend away
 157 from the layers.

158 We plot the plasmon dispersion along Γ -M (the Γ -K direction is not as interesting in the
 159 band structure) with the magnitude of the real part of \mathbf{q} ranging from $|\mathbf{q}|=q=0.007 \text{ \AA}^{-1}$ to
 160 0.21 \AA^{-1} , since both plasmon modes become very weak above $q=0.21 \text{ \AA}^{-1}$. The symmetric
 161 mode is more dispersive than antisymmetric, and varies as \sqrt{q} at small q , corresponding
 162 to classical plasmon with Drude behavior due to intraband transitions. Whereas the anti-
 163 symmetric mode varies almost linearly with q (has finite frequency at $q=0$) and relates to
 164 interband transitions between perfectly nested bands of the two layers⁴². In G/Li/G the
 165 plasmon frequencies are between 0.8 eV to 2.2 eV for $q \geq 0.007 \text{ \AA}^{-1}$; the antisymmetric
 166 mode is in the optical frequency range even at low q , whereas the symmetric mode enters
 167 into this range at higher q values. The symmetric mode is always lower in energy than the
 168 antisymmetric mode due to finite coupling⁴². We note that the acoustic plasmon arising
 169 from the anisotropy of the bands crossing the Fermi level along Γ -M is not captured in
 170 our calculations due to limitations of the frequency grid which is too coarse on the scale
 171 required to reveal this feature. However, this does not affect our conclusions since this
 172 particular mode is damped by the intraband transitions and therefore not of interest here.

173 We quantify the plasmon losses from the ratio of real to imaginary component of
 174 wavenumber, $\text{Re}[q]/\text{Im}[q]$ ⁴³, which corresponds to the number of plasmon wavelengths that
 175 propagate before it loses most of its energy [see Fig. 2(c)]. For the doping in G/Li/G ($E_F =$
 176 1.35 eV), a $\tau \approx 29 \text{ fs}$ was calculated using our methodology discussed above, which is much
 177 shorter in comparison with $\tau \approx 135 \text{ fs}$ for $E_F = 0.135 \text{ eV}$ ⁴³. We only give the ratio for the
 178 symmetric (intraband) mode in Fig. 2(c). Due to its linear dispersion, antisymmetric mode
 179 shows less variation in $\text{Re}[q]/\text{Im}[q]$ as compared with symmetric mode (see Supplemental
 180 Fig. S1³⁴). The in-plane propagation length of the plasmons varies directly with this ratio,
 181 with the symmetric plasmons propagating longer at longer wavelengths (λ_{air}). We also
 182 calculate the wave “shrinkage” or the field localization of the plasmons, shown in Fig. 2(c);
 183 this corresponds to the ratio by which the plasmon wavelength (λ_p) is smaller than that in
 184 vacuum, and is approximately 100 times for bilayer graphene.

185 There are three important decay modes that lead to plasmon damping: (i) Landau
 186 damping due to intraband losses when $\hbar\omega < \hbar v_F q$, (ii) interband losses (electron-hole
 187 transitions referred to as single-particle excitations, SPE’s, identified as poles of the re-
 188 sponse function^{42,44}) when $\hbar\omega > \hbar\omega_{\text{SPE}}$ (with damping region defined by $\hbar\omega_{\text{SPE}} - \hbar v_F q < \hbar\omega$
 189 $< \hbar\omega_{\text{SPE}} + \hbar v_F q$), and (iii) decay through optical phonons in graphene for $\omega > \omega_{\text{ph}}$ ($\omega_{\text{ph}} = 0.2$

190 eV or $6.2 \mu\text{m}$)⁴³ due to scattering of electrons (that is, plasmonic excitation) due to phonons.
 191 This calculation of dielectric function under the Random Phase Approximation (RPA) does
 192 not include the effects of electron-hole interactions, which are captured only by including
 193 a dynamically screened instead of the bare Coulomb interaction. However, these excitons
 194 give rise to a prominent peak in the absorption spectrum near 4.5 eV ⁴⁵ which is at a much
 195 higher energy than the visible frequency range. Also, doping has been shown to increase
 196 screening and reduce electron-hole interactions in graphene, leaving the optical response
 197 nearly identical to undoped graphene⁴⁵. Hence, the exclusion of electron-hole interactions
 198 in our calculations does not affect the results.

199 In case of G/Li/G, since the optical phonon $\omega_{\text{ph}} = 1400 \text{ cm}^{-1} \equiv 0.17 \text{ eV}$ ^{41,46} is much
 200 smaller than the symmetric or antisymmetric plasmon frequencies (0.8 eV to 2.2 eV for
 201 $q \geq 0.007 \text{ \AA}^{-1}$), only multiple scatterings by phonons (which are less likely) will scatter
 202 plasmons into the damping regions. On the other hand, plasmons within frequency range
 203 $\omega_{\text{SPE}} - \omega_{\text{ph}}$ to ω_{SPE} can get scattered by phonons into Landau/interband scattering regions.
 204 Therefore making $\omega > \omega_{\text{SPE}} - \omega_{\text{ph}}$ the region where plasmons are damped by interband
 205 transitions and optical phonons. The SPE's at $q = 0$ were identified at 0 eV , 0.6 eV and
 206 2.4 eV originating from the intraband, low energy interband and the electron-hole interband
 207 transitions in G/Li/G. The damping regions are defined by $E_{\text{SPE}} \pm \hbar v_{\text{F}} q \pm \hbar \omega_{\text{ph}}$ (including
 208 scattering by optical phonons), where v_{F} is the Fermi velocity and E_{SPE} is the single particle
 209 excitation energy^{44,47} [see gray shaded areas in Fig. 2(b)]. Heavy doping by lithium pushes
 210 the electron-hole interband threshold for the bilayer to $\omega_{\text{inter}} \approx 1.77 \text{ eV}$ ($\lambda = 0.7 \mu\text{m}$). Since
 211 the optical frequency range (ω_{op}) is between 1.59 eV to 3.26 eV ($\lambda = 0.38 \mu\text{m}$ to $0.78 \mu\text{m}$)
 212 and $\omega_{\text{inter}} < \omega_{\text{op}}$, most of the symmetric and antisymmetric plasmon modes in this range are
 213 not damped by the interband transitions, indicated by the shaded regions in Fig. 2(b) and
 214 2(e). Only for $q \geq 0.06 \text{ \AA}^{-1}$ are the symmetric and antisymmetric modes damped.

215 To push the interband threshold frequency, and hence the plasmon frequencies, higher
 216 into the optical range ($> 2 \text{ eV}$), the Fermi level needs to be moved farther into the conduction
 217 bands. Since the maximum possible intercalation in bilayer graphene corresponds to com-
 218 position C_{12}Li , additional Li can be incorporated only by having more than two graphene
 219 layers. We therefore explore trilayer graphene since it can accomodate two Li layers, with
 220 a composition Li_2C_{18} , which increases the doping level to $E_{\text{F}} = 1.51 \text{ eV}$. There are three
 221 modes in the trilayer structure in the $1.2 - 2.8 \text{ eV}$ frequency range along the Γ -M direction

222 for $q \geq 0.007 \text{ \AA}^{-1}$, two of which are symmetric and one antisymmetric, shown in Fig. 2(d).
 223 The third (second symmetric) mode emerges due to the third graphene layer which brings
 224 in additional nesting of the bands. Similar to the bilayer case, the first symmetric mode due
 225 to intraband excitations exhibits \sqrt{q} dependence and the other two modes disperse linearly,
 226 see Fig. 2(e). The loss function shows larger variations in the peak positions for the first
 227 symmetric mode due to \sqrt{q} behavior at low q as compared to the antisymmetric mode (see
 228 Supplemental Fig. S2 for details³⁴). More interestingly, the first symmetric and antisym-
 229 metric bands in the dispersion spectrum [red and blue curves in Fig. 2(e)] intersect and
 230 the symmetric and antisymmetric modes are degenerate for $q > 0.067 \text{ \AA}^{-1}$ along Γ -M. The
 231 reason behind this unusual degeneracy is the fine nesting between the bands at the Fermi
 232 level and consequently the absence of coupling between the two modes⁴².

233 The higher doping concentration pushes the interband threshold frequency (ω_{inter}) to
 234 $\approx 2.0 \text{ eV}$ (0.62 \mu m) for the first symmetric and antisymmetric modes in G/Li/G/Li/G.
 235 The poles at 0 eV, 0.64 eV, 0.93 eV and 2.5 eV correspond to the three damping regions
 236 associated with intraband, low energy interband, and higher energy electron-hole interband
 237 transitions. Hence, for $1.59 \text{ eV} < \omega < 2.0 \text{ eV}$ ($0.62 \text{ \mu m} < \lambda_{\text{air}} < 0.78 \text{ \mu m}$) the first symmetric
 238 and antisymmetric modes are undamped. More importantly, the second symmetric mode
 239 gets damped at a higher frequency ($\omega > 2.2 \text{ eV}$), so all three plasmon modes are undamped
 240 and emerge in the optical range for $q < 0.05 \text{ \AA}^{-1}$. The τ in graphene for such high doping
 241 concentration ($E_{\text{F}} = 1.51 \text{ eV}$) is quite small $\approx 19 \text{ fs}$ (See Supplemental Material³⁴). From the
 242 $\text{Re}[q]/\text{Im}[q]$ in Fig. 2(f), we find that the first symmetric mode can be observed further into
 243 the mid-infrared range (from extrapolation) ($\lambda_{\text{air}} > 3 \text{ \mu m}$), whereas the other two modes have
 244 shorter wavelengths ($\lambda_{\text{air}} < 0.62 \text{ \mu m}$). λ_{p} is also shrunk by approximately 100 times, Fig.
 245 2(f), as in the case for bilayer graphene, in agreement with previous reports⁴³. We only plot
 246 the ratio for the first symmetric (intraband) mode in Fig. 2(f). Since the antisymmetric and
 247 second symmetric modes disperse linearly, the variation in the $\text{Re}[q]/\text{Im}[q]$ is small. These
 248 plasmons exhibit similar “shrinkage” as that of the symmetric mode (refer to Supplemental
 249 Fig. S2 for further details³⁴).

250 Controlling the number of layers and the concentration of intercalated Li atoms appears to
 251 be a feasible method for engineering the properties of visible plasmons for applications. For
 252 example, the mid-infrared region plasmons in both the bilayer and trilayer Li-intercalated
 253 structures, can be used for plasmonic biosensing^{4,16}. We caution that certain technical

254 aspects of the calculations reported here, like the choice of exchange correlation functional
255 for the electronic structure, can affect the electronic spectrum and can shift the plasmon
256 energies to slightly different values than what we reported; such shifts could change the
257 precise values of the damped plasmon frequencies but we do not expect them to alter the
258 overall picture. Damping due to the presence of defects and substrate phonons, features that
259 were not included in the model of the physical system considered here, can also influence
260 the existence of undamped 2D plasmons in the visible frequency range. A detailed analysis
261 of these parameters will constitute the future scope of this work. Our work can be easily
262 extended to explore other multilayers of other 2D materials (such as black phosphorus,
263 transition metal dichalcogenides) with different dopants and/or intercalants (K, Mg, Na
264 etc), opening up new pathways for fine tuning the plasmon dispersion either by varying
265 the number and type of layers, and/or by varying the concentration and type of intercalant
266 atoms.

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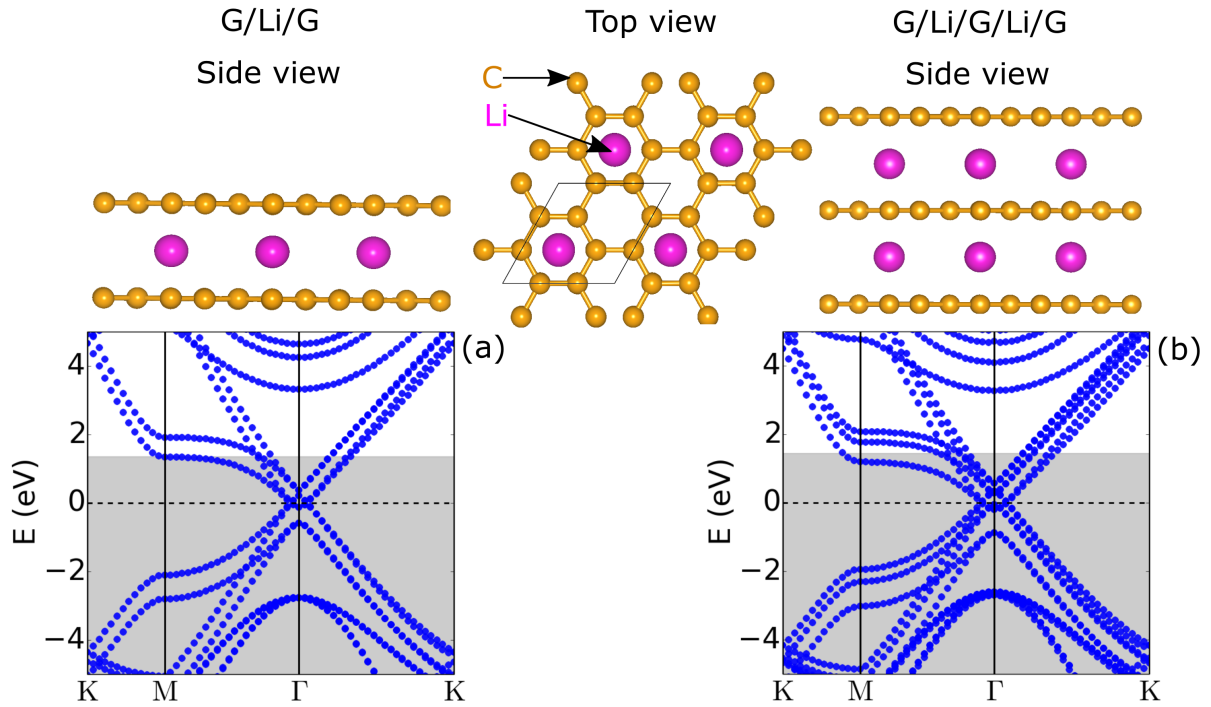


FIG. 1. Atomic structures (side and top views) and electronic structures of: (a) the bilayer Li-intercalated graphene (G/Li/G, left) and (b) the trilayer Li-intercalated graphene (G/Li/G/Li/G, right). The shaded regions in (a) and (b) denote the occupied states, and the dashed black lines the Dirac point / Fermi level in undoped layers.

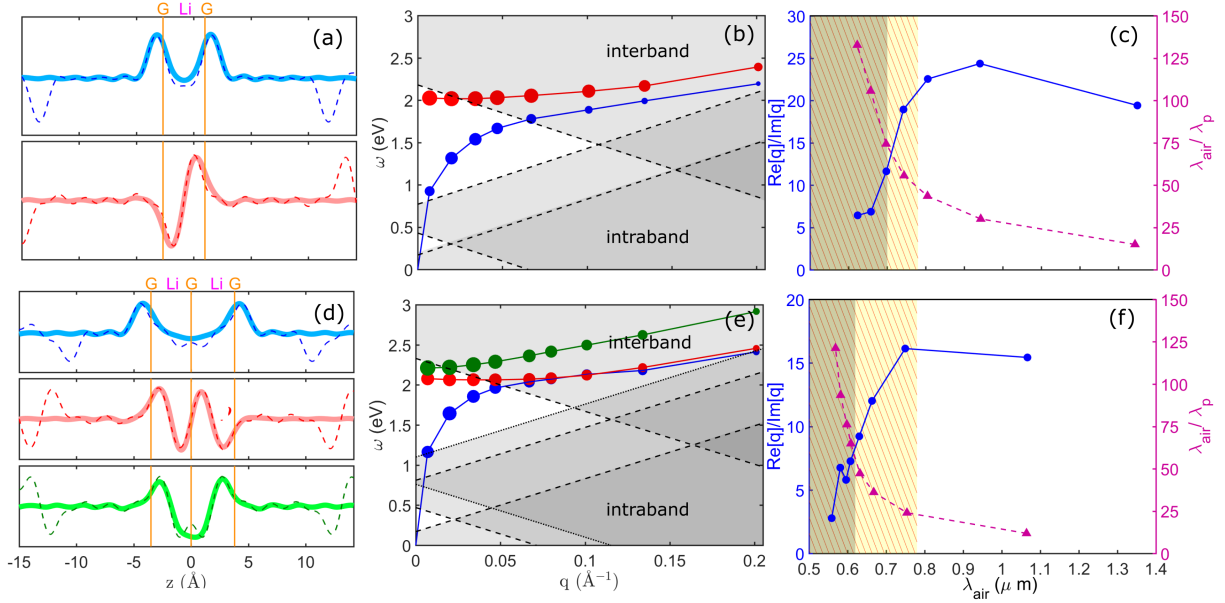


FIG. 2. Plasmon features for: (a)-(c), the G/Li/G system, and (d)-(f), the G/Li/G/Li/G system. (a) and (d) Plasmon charge density $\rho(\mathbf{r})$ at $q=0.007 \text{ \AA}^{-1}$ for the symmetric modes (blue and green lines) and the antisymmetric mode (red lines); solid lines (thicker and lighter shade) are for results with transparent boundary conditions, dashed lines (thinner and darker shade) for periodic boundary conditions with Coulomb cutoff (see text). (b) and (e) Dispersion relation of plasmons along the Γ to M direction; the diameter of the circles is proportional to the strength of the resonance¹⁸. Shaded areas represent regions of inter- and intra-band losses (including damping by optical phonon). (c) and (f) $\text{Re}[q]/\text{Im}[q]$ (left axis, solid line in blue), and field localization (right axis, dashed line in magenta), or “shrinkage”, of the lowest symmetric mode. τ is ≈ 29 fs and 19 fs for the G/Li/G and the G/Li/G/Li/G systems, respectively. The grey shaded areas denote the region of inter-band losses, and the yellow shaded (hatched) areas denote the visible frequency range, calculated with the Fermi velocity of graphene.

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